- 1. You are given a *p*-type doped silicon crystal and are asked to make an ohmic contact. What material would you use? (refer to Appendix 4)
- 2. Describe the energy bands for a metal and a semiconductor *before* and *after* contact.
 - (a) *n*-type, $\phi_{\rm M} > \phi_{\rm S}$
 - (b) *n*-type, $\phi_{\rm M} < \phi_{\rm S}$
 - (c) *p*-type, $\phi_{\rm M} > \phi_{\rm S}$
 - (d) *p*-type, $\phi_{\rm M} < \phi_{\rm S}$
- 3. Calculate the room-temperature saturation current and the forward current at 0.3 V for a silver/*n*-doped silicon Schottky-type diode. Take for the active area of 10^{-8} m² and $C = 10^{19}$ A/m²K².